



H2W5-850

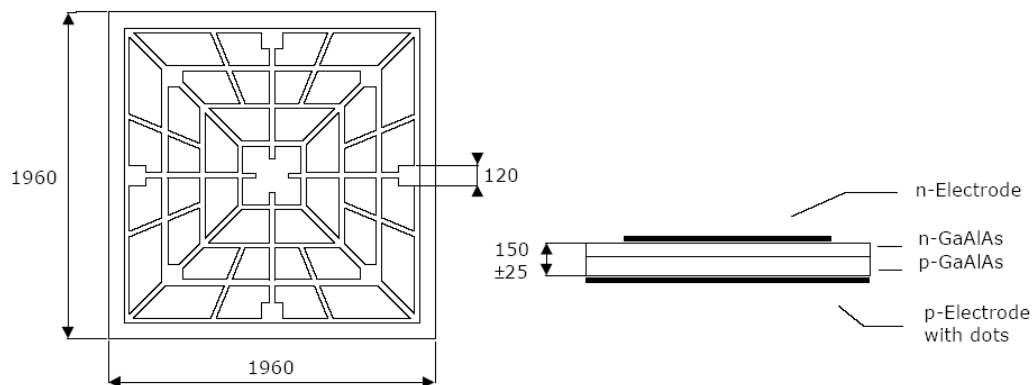


- optical power: 550 mW at 2 A
- beam angle: +/-75°, lambertian high dome lens
- compatibel with many collimating optics
- chip size 2 x 2mm
- 20mm diameter aluminium groundplate

chip-die specification:

1. This specification applies to GaAlAs / GaAlAs Chips (substrate removed)
2. Structure
 - 2.1 Mesa structure
 - 2.2 Electrodes

p-side (anode)	Au alloy
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	Min	typ	max	Unit
Forward voltage	V_F	$I_F = 100 \text{ mA}$		1,40	1,60	V
Reverse current	I_R	$V_R = 5 \text{ V}$			10	μA
Radiant intensity	I_e	$I_F = 100 \text{ mA}$		5,0		mW/sr
Special bandwidth at 50%	$\Delta\lambda_{0,5}$	$I_F = 100 \text{ mA}$		38		nm
Switching time	t_r, t_f	$I_F = 100 \text{ mA}$		35		ns
Peak wavelength	λ	$I_F = 100 \text{ mA}$		850		nm



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